

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

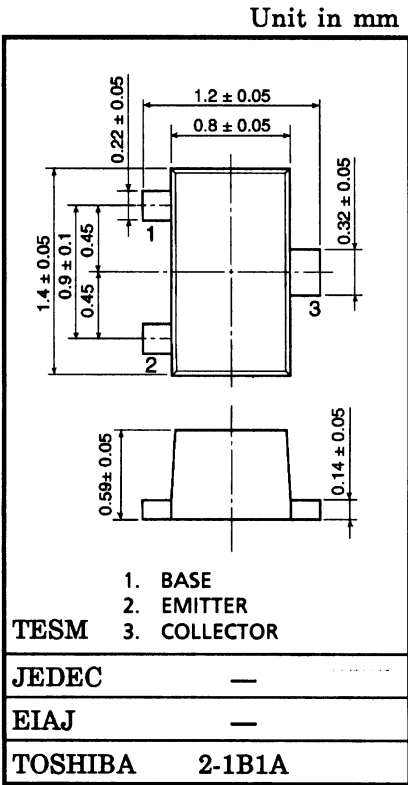
2SC4738FT

Audio Frequency General Purpose Amplifier Applications

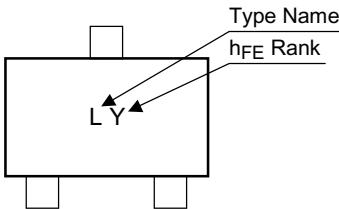
- High Voltage: $V_{CEO} = 50\text{ V}$
- High Current: $I_C = 150\text{ mA (max)}$
- High h_{FE} : $h_{FE} = 120\text{ to }400$
- Excellent h_{FE} Linearity: $h_{FE}(I_C = 0.1\text{ mA})/h_{FE}(I_C = 2\text{ mA}) = 0.95\text{ (typ.)}$
- Complementary to 2SA1832FT

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	150	mA
Base current	I_B	30	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55 to 125	°C



Marking



000630EAA1

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Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 60\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	μA
DC current gain	h_{FE} (Note)	$V_{CE} = 6\text{ V}, I_C = 2\text{ mA}$	120	—	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\text{ mA}, I_B = 10\text{ mA}$		0.1	0.25	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 1\text{ mA}$	80	—	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	2.0	3.5	pF

Note: h_{FE} Classification Y (Y): 120 to 240, GR (G): 200 to 400

() Marking symbol

